# 3.3 V Dual Differential LVPECL/LVDS/CML to LVTTL/LVCMOS Translator

#### Description

The MC100EPT23 is a dual differential LVPECL/LVDS/CML to LVTTL/LVCMOS translator. Because LVPECL (Positive ECL), LVDS, and positive CML input levels and LVTTL/LVCMOS output levels are used, only + 3.3 V and ground are required. The small outline 8-lead SOIC package and the dual gate design of the EPT23 makes it ideal for applications which require the translation of a clock or data signal.

The EPT23 is available in only the ECL 100K standard. Since there are no LVPECL outputs or an external  $V_{BB}$  reference, the EPT23 does not require both ECL standard versions. The LVPECL/LVDS inputs are differential. Therefore, the MC100EPT23 can accept any standard differential LVPECL/LVDS input referenced from a  $V_{CC}$  of + 3.3 V.

#### **Features**

- 1.5 ns Typical Propagation Delay
- Maximum Operating Frequency > 275 MHz
- LVPECL/LVDS/CML Inputs, LVTTL/LVCMOS Outputs
- 24 mA LVTTL Outputs
- Operating Range:
  - $V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V} \text{ with GND} = 0 \text{ V}$
- These Devices are Pb-Free, Halogen Free and are RoHS Compliant



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751-07





TSSOP-8 DT SUFFIX CASE 948R-02

DFN-8 MN SUFFIX CASE 506AA

#### **MARKING DIAGRAMS\***







A = Assembly Location

= Pb-Free Package

(Note: Microdot may be in either location)

\*For additional marking information, refer to Application Note <u>AND8002/D</u>.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC100EPT23DG	SOIC-8 NB (Pb-Free)	98 Units/Tube
MC100EPT23DR2G	SOIC-8 NB (Pb-Free)	2500/Tape & Reel
MC100EPT23DTG	TSSOP-8 (Pb-Free)	100 Units/Tube
MC100EPT23DTR2G	TSSOP-8 (Pb-Free)	2500/Tape & Reel
MC100EPT23MNR4G	DFN-8 (Pb-Free)	1000/Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, <a href="https://example.com/BRD8011/D">BRD8011/D</a>.

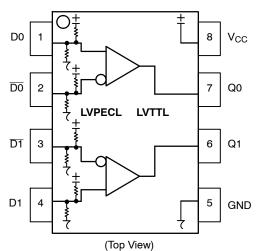


Figure 1. Logic Diagram and 8-Lead Pinout

#### **Table 1. PIN DESCRIPTION**

Pin	Function
Q0, Q1	LVTTL/LVCMOS Outputs
D0**, D1** D0**, D1**	Differential LVPECL/LVDS/CML Inputs
V <sub>CC</sub>	Positive Supply
GND	Ground
EP	(DFN-8 only) Thermal exposed pad must be connected to a sufficient thermal conduit. Electrically connect to the most negative supply (GND) or leave unconnected, floating open.

<sup>\*\*</sup> Pins will default to  $V_{\mbox{\footnotesize CC}}/2$  when left open.

#### Table 2. ATTRIBUTES

Characteristics	Value
Internal Input Pulldown Resistor	50 kΩ
Internal Input Pullup Resistor	50 kΩ
ESD Protection Human Body Model Machine Model Charged Device Model	> 1500 V > 100 V > 2 kV
Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1)	Pb-Free Pkg
SOIC-8 NB TSSOP-8 DFN-8	Level 1 Level 3 Level 1
Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in
Transistor Count	91 Devices
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test	•

<sup>1.</sup> For additional information, see Application Note AND8003/D.

#### **Table 3. MAXIMUM RATINGS**

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V <sub>CC</sub>	Power Supply	GND = 0 V		3.8	V
VI	Input Voltage	GND = 0 V	$V_I \leq V_{CC}$	3.8	V
l <sub>out</sub>	Output Current	Continuous Surge		50 100	mA
T <sub>A</sub>	Operating Temperature Range			-40 to +85	°C
T <sub>stg</sub>	Storage Temperature Range			-65 to +150	°C
θJA	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	SOIC-8 NB	190 130	°C/W
θЈС	Thermal Resistance (Junction-to-Case)	Standard Board	SOIC-8 NB	41 to 44	°C/W
θJA	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	TSSOP-8	185 140	°C/W
θJC	Thermal Resistance (Junction-to-Case)	Standard Board	TSSOP-8	41 to 44	°C/W
θJA	Thermal Resistance (Junction-to-Ambient)	0 lfpm 500 lfpm	DFN-8	129 84	°C/W

#### **Table 3. MAXIMUM RATINGS**

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
T <sub>sol</sub>	Wave Solder (Pb-Free)	<2 to 3 sec @ 260°C		265	°C
$\theta_{\sf JC}$	Thermal Resistance (Junction-to-Case)	(Note 1)	DFN-8	35 to 40	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. JEDEC standard multilayer board – 2S2P (2 signal, 2 power)

Table 4. PECL DC CHARACTERISTICS (V<sub>CC</sub> = 3.3 V, GND = 0 V (Note 1))

			-40°C		25°C		85°C				
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
I <sub>CCH</sub>	Power Supply Current (Outputs set to HIGH)	10	20	35	10	20	35	10	20	35	mA
I <sub>CCL</sub>	Power Supply Current (Outputs set to LOW)	15	27	40	15	27	40	15	27	40	mA
V <sub>IH</sub>	Input HIGH Voltage	2075		2420	2075		2420	2075		2420	mV
V <sub>IL</sub>	Input LOW Voltage	1355		1675	1355		1675	1355		1675	mV
V <sub>IHCMR</sub>	Input HIGH Voltage Common Mode Range (Note 2)	1.2		3.3	1.2		3.3	1.2		3.3	V
I <sub>IH</sub>	Input HIGH Current			150			150			150	μΑ
I <sub>IL</sub>	Input LOW Current D D	-150 -150			-150 -150			-150 -150		0.5	μΑ

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

- 1. All values vary 1:1 with V<sub>CC</sub>.
- V<sub>IHCMR</sub> min varies 1:1 with V<sub>EE</sub>, V<sub>IHCMR</sub> max varies 1:1 with V<sub>CC</sub>. The V<sub>IHCMR</sub> range is referenced to the most positive side of the differential input signal.

Table 5. LVTTL/LVCMOS OUTPUT DC CHARACTERISTICS (V<sub>CC</sub> = 3.3 V, GND = 0.0 V, T<sub>A</sub> = -40°C to 85°C)

Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V <sub>OH</sub>	Output HIGH Voltage	I <sub>OH</sub> = -3.0 mA	2.4			V
V <sub>OL</sub>	Output LOW Voltage	I <sub>OL</sub> = 24 mA			0.5	V
los	Output Short Circuit Current		-180		-50	mA

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

Table 6. AC CHARACTERISTICS (V<sub>CC</sub> = 3.0 V to 3.6 V, GND = 0.0 V (Note 1))

			-40°C 25°C		85°C						
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
f <sub>max</sub>	Maximum Frequency (Figure 2)	275	350		275	350		275	350		MHz
t <sub>PLH</sub> , t <sub>PHL</sub>	Propagation Delay to Output Differential (Note 2)	1.1	1.5	1.8	1.1	1.5	1.8	1.1	1.5	1.8	ns
t <sub>SK++</sub> t <sub>SK</sub> t <sub>SKPP</sub>	Output-to-Output Skew++ Output-to-Output Skew Part-to-Part Skew (Note 3)		15 35 70	60 80 500		15 40 70	70 80 500		30 40 140	125 80 500	ps
t <sub>JITTER</sub>	Random Clock Jitter (RMS) (Figure 2)		5	10		5	10		5	10	ps
$V_{PP}$	Input Voltage Swing (Differential Configuration)	150	800	1200	150	800	1200	150	800	1200	mV
t <sub>r</sub> t <sub>f</sub>	Output Rise/Fall Times (0.8 V – 2.0 V) Q, Q	330	600	900	330	600	900	330	650	900	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

- 1. Measured with a 750 mV 50% duty-cycle clock source.  $R_L = 500 \Omega$  to GND and  $C_L = 20 pF$  to GND. Refer to Figure 3.
- 2. Reference ( $V_{CC} = 3.3V \pm 5\%$ ; GND = 0 V)
- 3. Skews are measured between outputs under identical conditions.

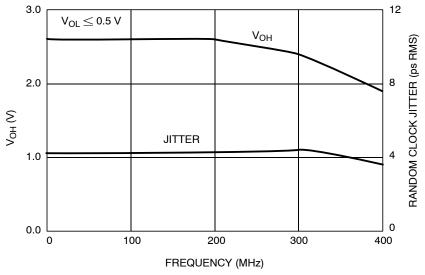


Figure 2. Typical V<sub>OH</sub> / Jitter Versus Frequency (25°C)

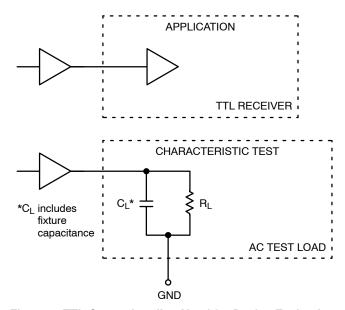


Figure 3. TTL Output Loading Used for Device Evaluation

#### **Resource Reference of Application Notes**

AN1405/D **ECL Clock Distribution Techniques** AN1406/D Designing with PECL (ECL at +5.0 V) AN1503/D ECLinPS™ I/O SPiCE Modeling Kit Metastability and the ECLinPS Family AN1504/D AN1568/D Interfacing Between LVDS and ECL - The ECL Translator Guide AN1672/D AND8001/D -**Odd Number Counters Design** AND8002/D -Marking and Date Codes AND8020/D -Termination of ECL Logic Devices AND8066/D Interfacing with ECLinPS

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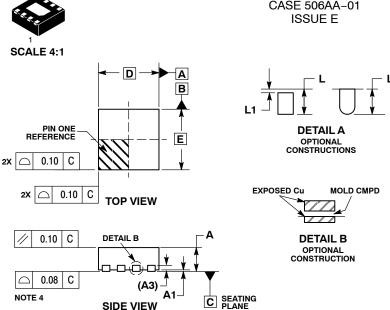
AND8090/D - AC Characteristics of ECL Devices

DETAIL A

e

- D2 →

**BOTTOM VIEW** 



0.10 C

Ф

AB

0.05 C NOTE 3



**DATE 22 JAN 2010** 

#### NOTES

- DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994 . CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN
- 0.15 AND 0.20 MM FROM TERMINAL TIP. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MULIMETERS					
	MILLIMETERS					
DIM	MIN	MAX				
Α	0.80	1.00				
A1	0.00	0.05				
A3	0.20	REF				
b	0.20	0.30				
D	2.00	BSC				
D2	1.10	1.30				
E	2.00	BSC				
E2	0.70	0.90				
е	0.50	BSC				
K	0.30	REF				
L	0.25	0.35				
L1		0.10				

#### **GENERIC MARKING DIAGRAM\***



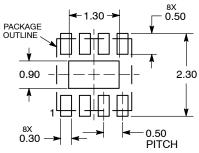
XX = Specific Device Code

= Date Code = Pb-Free Device

\*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " ■", may or may not be present.

#### **RECOMMENDED SOLDERING FOOTPRINT\***



**DIMENSIONS: MILLIMETERS** 

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	DFN8, 2.0X2.0, 0.5MM PITO	CH	PAGE 1 OF 1			

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SOIC-8 NB CASE 751-07 **ISSUE AK** 

**DATE 16 FEB 2011** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIMETERS		ERS INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.80	5.00	0.189	0.197	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.053	0.069	
D	0.33	0.51	0.013	0.020	
G	1.27	7 BSC	0.050 BSC		
Н	0.10	0.25	0.004	0.010	
J	0.19	0.25	0.007	0.010	
K	0.40	1.27	0.016	0.050	
М	0 °	8 °	0 °	8 °	
N	0.25	0.50	0.010	0.020	
S	5.80	6.20	0.228	0.244	

#### **SOLDERING FOOTPRINT\***



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Assembly Location

= Wafer Lot = Year = Work Week

= Pb-Free Package



XXXXXX = Specific Device Code = Assembly Location Α

= Year ww = Work Week

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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#### SOIC-8 NB CASE 751-07 ISSUE AK

## DATE 16 FEB 2011

STYLE 4: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 2 4. ANODE 5. ANODE #2 6. ANODE #2 7. ANODE #1 8. COMMON CATHODE
STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 STAGE Vd 7. EMITTER, #1 AGE Vd 8. COLLECTOR, #1
STYLE 12:  1 PIN 1. SOURCE 2 SOURCE 2 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COMMON 6. COLLECTOR, DIE #2 6. COMMON 7. COLLECTOR, DIE #1 6. COMMON 8. COLLECTOR, DIE #1
STYLE 20:  1 PIN 1. SOURCE (N) 2. GATE (N) 2 3. SOURCE (P) 4. GATE (P) 5. DRAIN 2 6. DRAIN 7. DRAIN 1 8. DRAIN
STYLE 24:
STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND E 5. V_MON E 6. VBULK E 7. VBULK 8. VIN

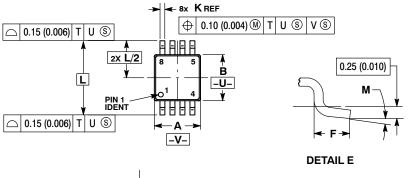
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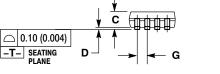
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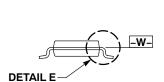


#### **TSSOP 8 CASE 948R-02 ISSUE A**

#### **DATE 04/07/2000**







- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH. OR GATE BURRS SHALL NOT EXCEED 0.15
- (0.006) PER SIDE.
  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
  5. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
  6. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.114	0.122
В	2.90	3.10	0.114	0.122
С	0.80	1.10	0.031	0.043
D	0.05	0.15	0.002	0.006
F	0.40	0.70	0.016	0.028
G	0.65 BSC		0.026	BSC
K	0.25	0.40	0.010	0.016
L	4.90 BSC		0.193	BSC
M	٥°	6 °	٥°	6°

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